

MDM1000E33E2

FEATURES

- * Low noise due to ultra soft fast recovery diode.
- * High reliability, high durability diodes.
- * Isolated heat sink (terminal to base).

ABSOLUTE MAXIMUM RATINGS (T_C=25°C)

Item	Symbol	Unit	MDM1000E33E2
Repetitive Peak Reverse Voltage	V _{RRM}	V	3,300
Forward Current	DC	A	1,000
	1ms		2,000
Operating Junction Temperature	T _{vj op}	°C	-40 ~ +150
Storage Temperature	T _{stg}	°C	-40 ~ +125
Isolation Test Voltage	Terminals-base	V _{ISO}	V _{RMS}
	Terminal 1-Terminal 2		
Screw Torque	Terminals (M8)	-	N·m
	Mounting (M6)		
			6 (2)

Notes: (1) Recommended Value 15⁺⁰₋₃N·m

(2) Recommended Value 5.5±0.5N·m

ELECTRICAL CHARACTERISTICS

Item	Symbol	Unit	Min.	Typ.	Max.	Test Conditions
Repetitive Reverse Current	I _{RRM}	mA	-	2.5	25	V _R =3,300V, T _{vj} =125°C
Forward Voltage Drop	V _F	V	-	2.5	3.0	I _F =1,000A, T _{vj} =125°C
			-	2.5	-	I _F =1,000A, T _{vj} =150°C
Reverse Recovery Time	t _{rr}	μs	-	0.7	1.2	T _{vj} =125°C
Reverse Recovery Loss	E _{rr(10%)}	J/P	-	1.6	2.3	V _R =1,650V, I _F =1,000A, L _S =100nH, R _G =3.3Ω (3)
	E _{rr(full)}		-	2.0	-	
			-	2.3	-	T _{vj} =150°C

Notes: (3) Counter arm; MBN1200E33D V_{GE}=+/-15VR_G value is the test condition's value for evaluation of the switching times, not recommended value.Please, determine the suitable R_G value after the measurement of switching waveforms

(overshoot voltage, etc.) with appliance mounted

PACKAGE CHARACTERISTICS

Item	Symbol	Unit	Min.	Typ.	Max.	Test Conditions
Terminal Resistance	R _{Ce}	mΩ	-	0.2	-	per arm, T _{vj} =25°C
Stray inductance module	L _{SCE}	nH	-	21	-	per arm
Thermal Impedance	R _{th(j-c)}	K/W	-	-	0.017	Junction to case (per arm)
Comparative tracking index	CTI		-	600	-	
Contact Thermal Impedance	R _{th(c-f)}	K/W	-	0.008	-	Case to fin (λgrease=1W/(m·K), Heat-sink flatness ≤50um)

* Please contact our representatives at order.

* For improvement, specifications are subject to change without notice.

* For actual application, please confirm this spec sheet is the newest revision.

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DEFINITION OF TEST CIRCUIT

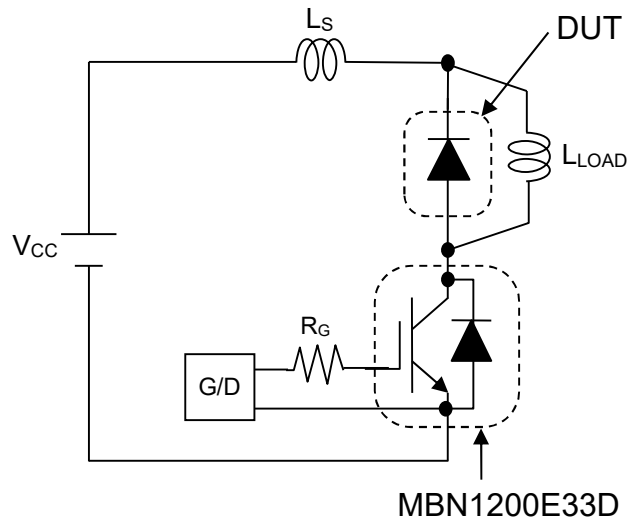


Fig.1 Switching test circuit

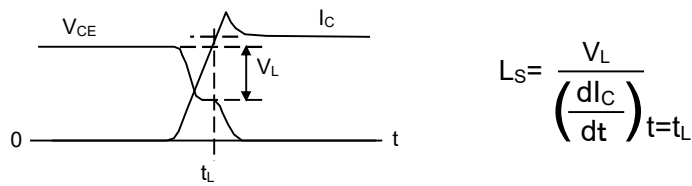
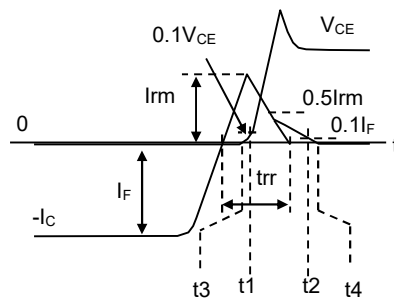


Fig.2 Definition of stray inductance



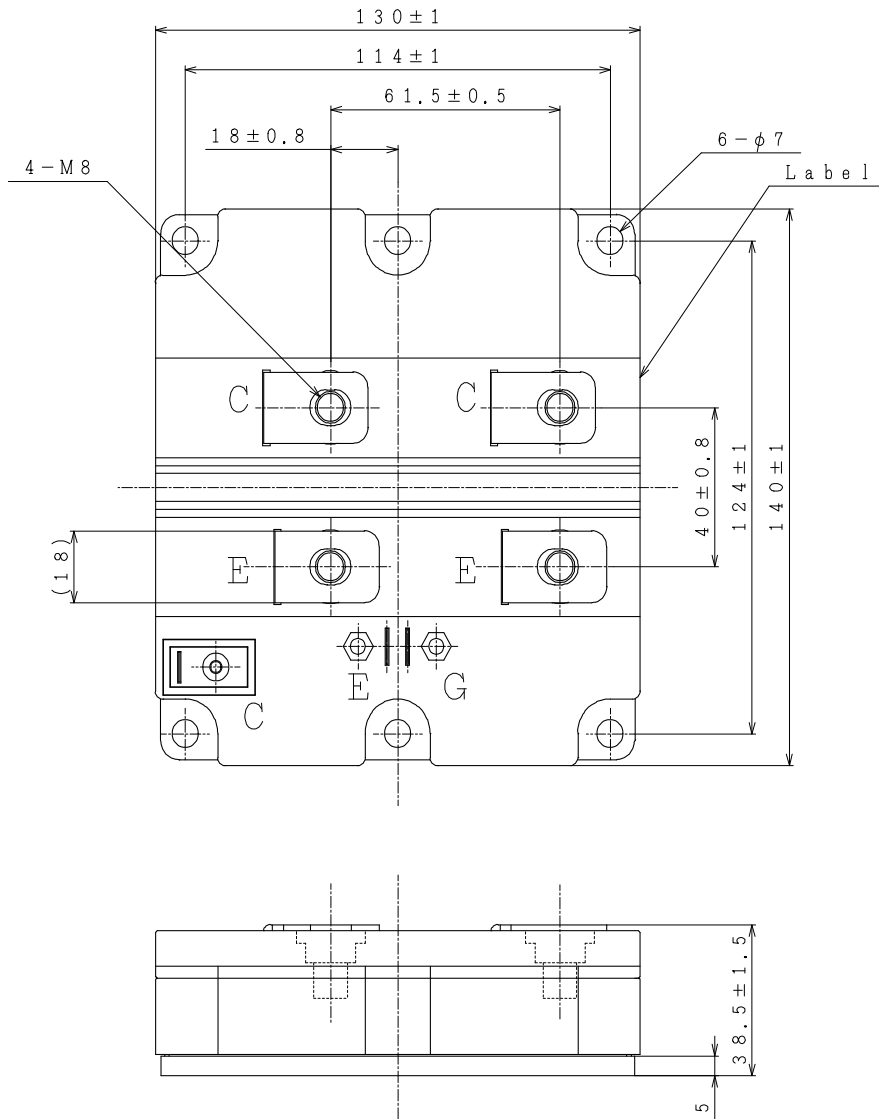
$$E_{rr(10\%)} = \int_{t_1}^{t_2} I_F \cdot V_{CE} dt$$

$$E_{rr(full)} = \int_{t_3}^{t_4} I_F \cdot V_{CE} dt$$

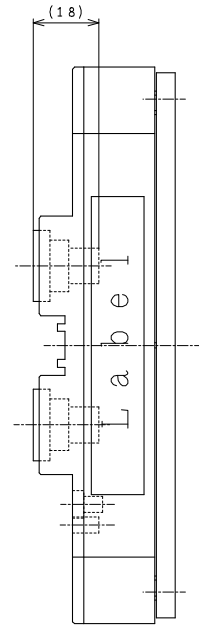
Fig.3 Definition of switching loss

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OUTLINE DRAWING

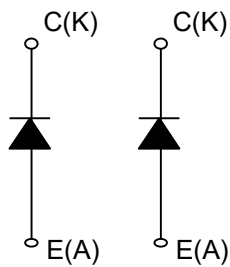


Unit in mm

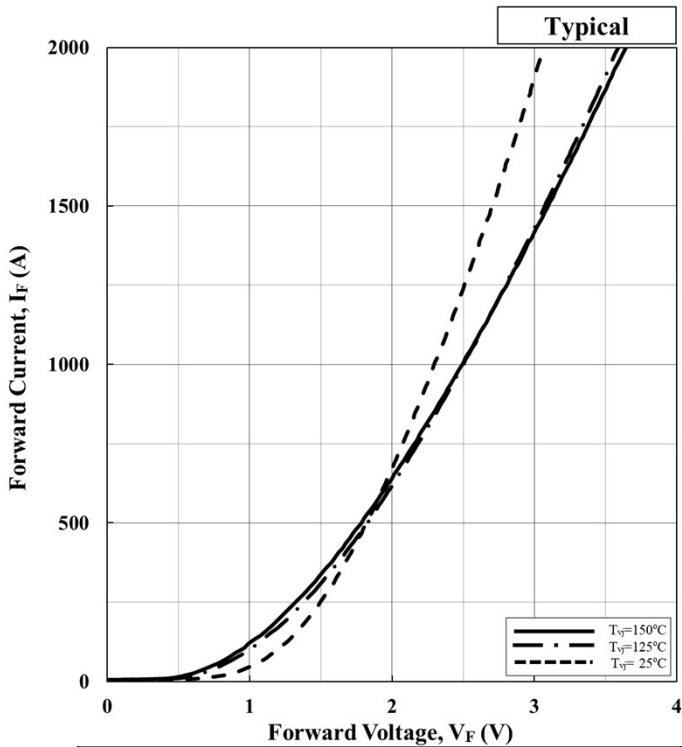


Weight: 900g

CIRCUIT DIAGRAM



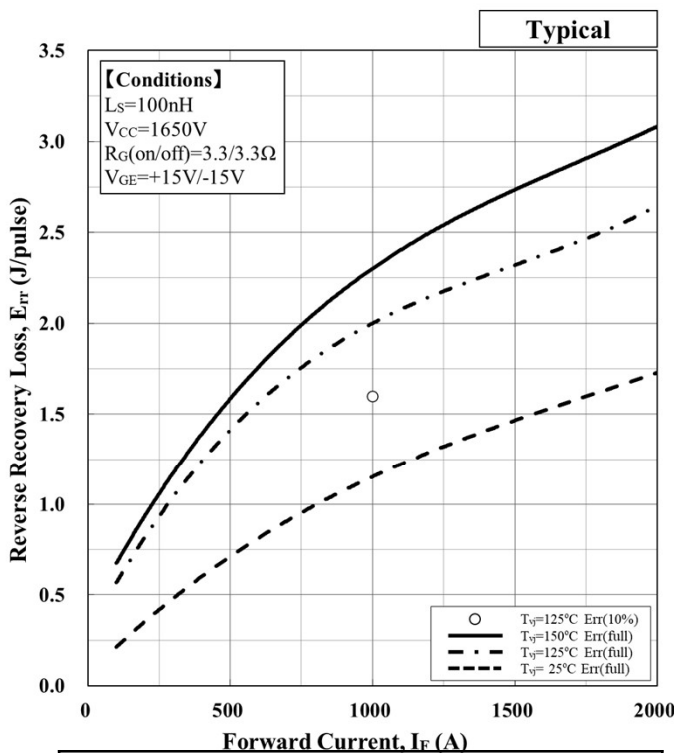
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$$V_F[V] = a_3 \cdot |I_F|^3 + a_2 \cdot |I_F|^2 + a_1 \cdot |I_F| + a_0$$

Temp.[°C]	a_3	a_2	a_1	a_0
25	1.56E-10	-6.95E-07	1.77E-03	1.08E+00
125	1.81E-10	-8.35E-07	2.33E-03	8.32E-01
150	1.78E-10	-8.23E-07	2.38E-03	7.64E-01

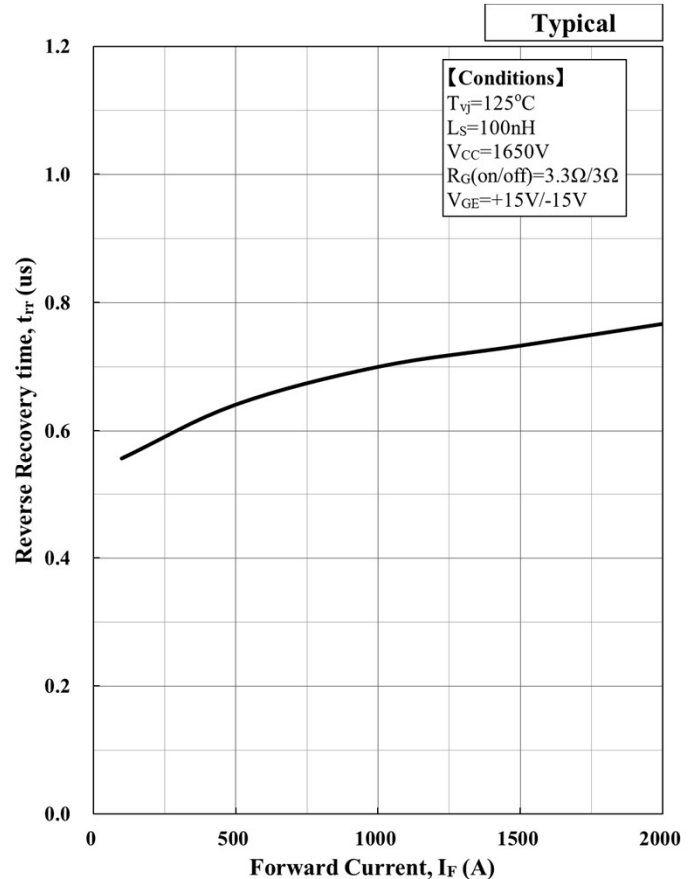
Forward Current vs. Forward Voltage
(Measured at main terminal)



$$E [J] = a_3 \cdot |I_F|^3 + a_2 \cdot |I_F|^2 + a_1 \cdot |I_F| + a_0$$

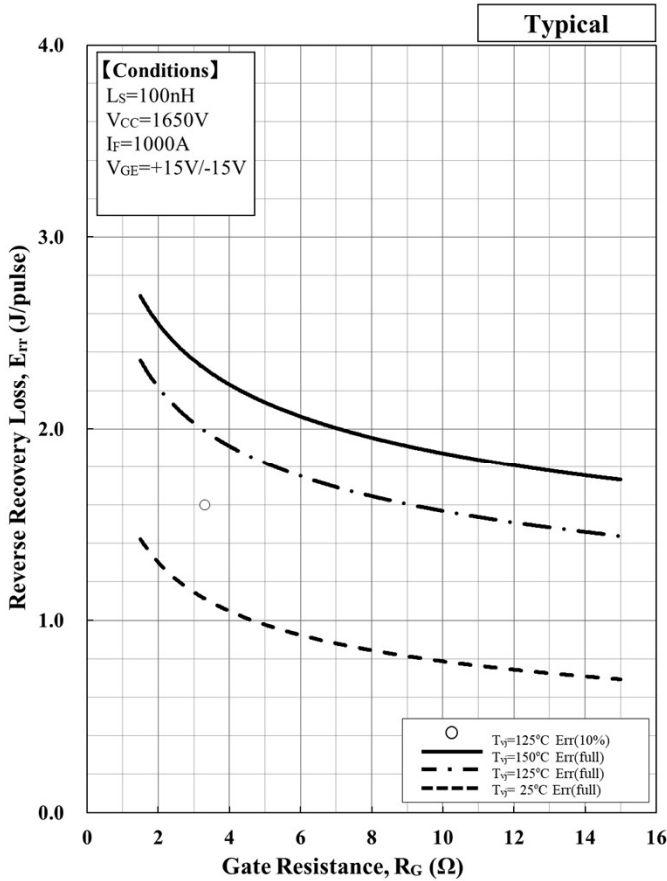
Temp.[°C]	a_3	a_2	a_1	a_0
25	1.05E-10	-5.74E-07	1.56E-03	6.33E-02
125	3.64E-10	-1.63E-06	2.98E-03	2.86E-01
150	2.64E-10	-1.36E-06	3.01E-03	3.88E-01

Recovery loss vs. Forward current

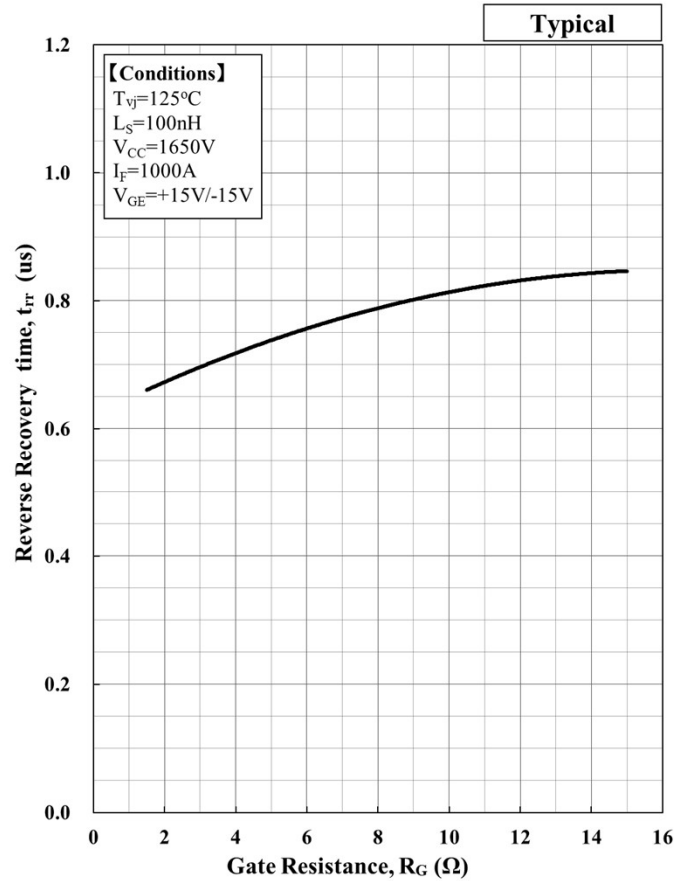


Reverse Recovery time vs. Forward current

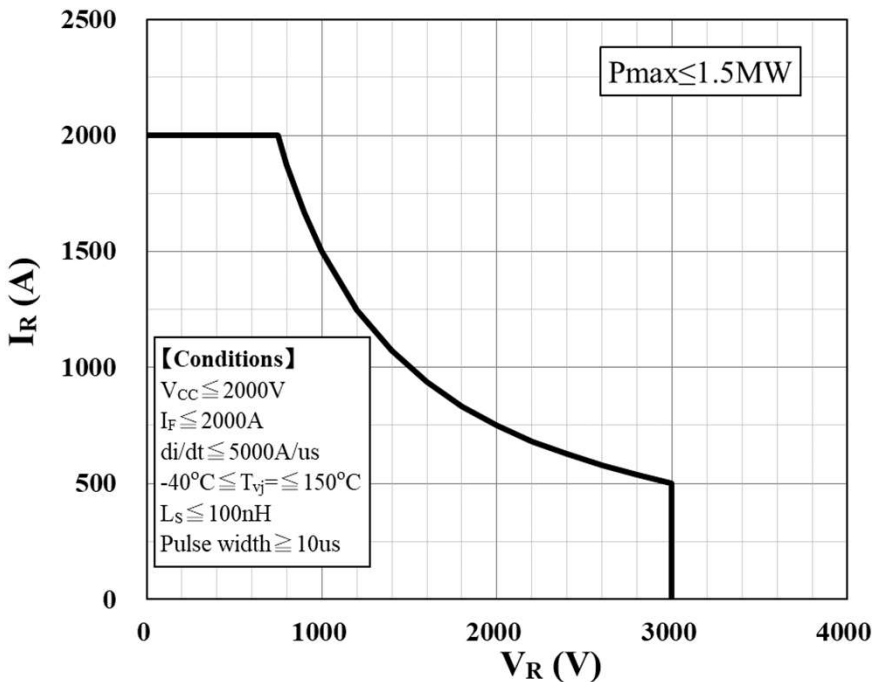
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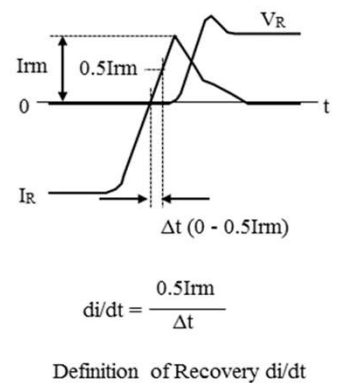
Reverse Recovery loss vs. Gate Resistance



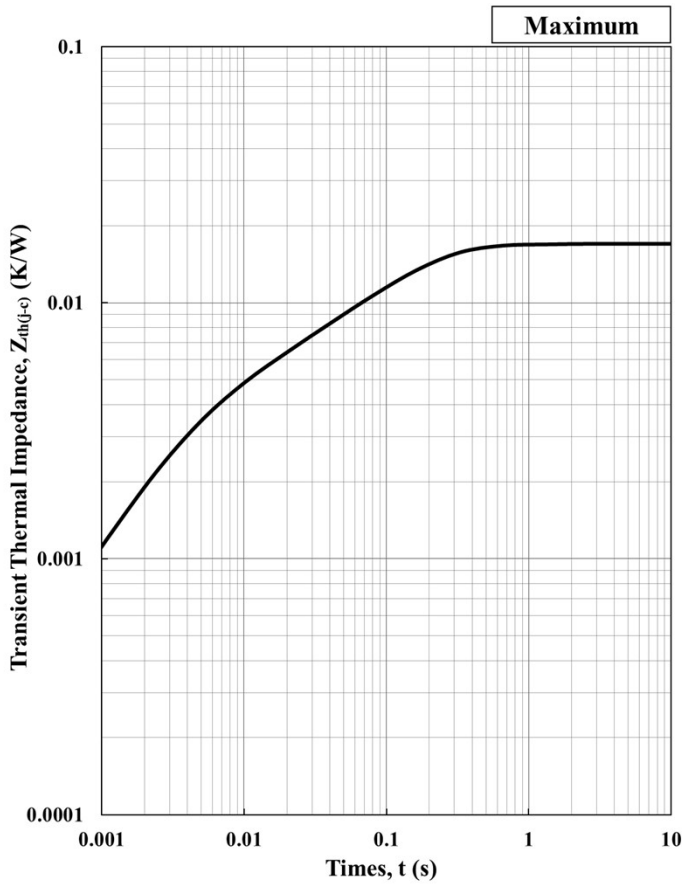
Reverse Recovery time vs. Gate Resistance



(Defined at power terminals)
 Reverse Recovery Safe Operation Area (RRSOA)



MDM1000E33E2



Transient Thermal Impedance Curve

Foster model lumped circuit constant

n	1	2	3	4	Unit
R th, Diode [n]	1.03E-02	2.88E-03	3.29E-03	5.06E-04	[K/W]
C th, Diode [n]	1.48E+01	1.05E+01	1.41E+00	1.77E+00	[J/K]

Cauer model lumped circuit constant

n	1	2	3	4	Unit
R th, Diode [n]	2.63E-03	3.03E-03	6.16E-03	5.14E-03	[K/W]
C th, Diode [n]	6.96E-01	9.82E-01	6.22E+00	1.79E+01	[J/K]

Material declaration

Please note the following materials are contained in the product, in order to keep characteristic and reliability level.

Material	Contained part
Lead (Pb) and its compounds	Solder

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Minebea POWER SEMICONDUCTORS

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1. Since mishandling of semiconductor devices may cause malfunctions, please be sure to read "Precautions for Safe Use and Notices" in the individual brochure before use.
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8. For handling other than described in this manual, follow the handling instructions (IGBT-HI-00002).

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- For inquiries relating to the products, please contact nearest representatives that is located "Inquiry" portion on the top page of a home page.
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